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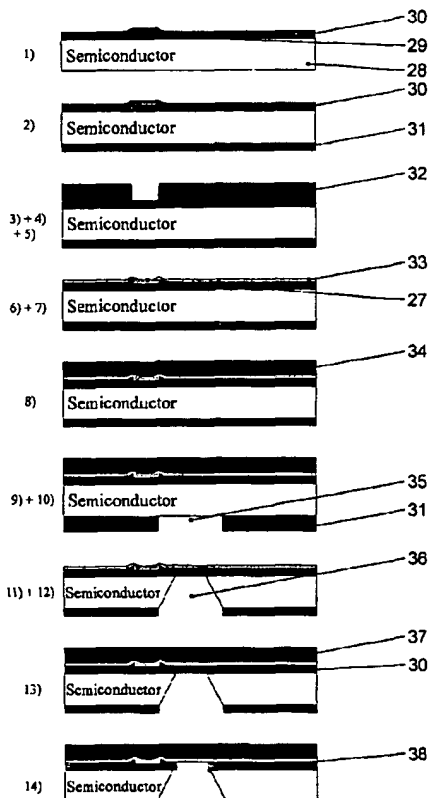
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(54) Title: FIELD-THROUGH PROCESS AND AMPLIFIER WITH FIELD-THROUGH



(57) Abstract: The invention concerns a process for generating a feed-through in a semiconductor wafer, which has electric circuitry embedded in a front surface whereby the hole for the feed-through is generated by the combined use of a front side protection layer and a wet KOH etch process etching the hole from the back side of the wafer, where a photomasking process is subsequently used to define the via followed by deposition of the via material.

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